

# Theoretical investigations of superlattice band structure approximation

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Citation Report

#	ARTICLE	IF	CITATIONS
1	Magneto-Optical Investigations of a Novel Superlattice: HgTe-CdTe. Physical Review Letters, 1983, 51, 907-910.	2.9	181
2	Advantages of the HgTe/CdTe superlattice as an infrared detector material. Applied Physics Letters, 1983, 43, 180-182.	1.5	179
3	Electronic structure and semiconductor-semimetal transition in InAs-GaSb superlattices. Physical Review B, 1983, 28, 842-845.	1.1	350
4	Modification of optical properties of GaAs/Ga <sup>1-x</sup> Al <sub>x</sub> As superlattices due to band mixing. Applied Physics Letters, 1983, 43, 536-538.	1.5	144
5	Short wavelength (visible) GaAs quantum well lasers grown by molecular beam epitaxy. Applied Physics Letters, 1984, 45, 16-18.	1.5	53
6	Electronic structure of PbTe/Pb <sup>1-x</sup> Sn <sub>x</sub> Te superlattices. Physical Review B, 1984, 30, 3394-3405.	1.1	81
7	Optical selection rules in superlattices in the envelope-function approximation. Physical Review B, 1984, 29, 935-941.	1.1	99
8	Optical studies of semiconductor superlattices. Surface Science, 1984, 142, 460-473.	0.8	10
9	Magneto-optics in a II-VI superlattice: HgTe-CdTe. Surface Science, 1984, 142, 593-597.	0.8	5
10	CONDUCTION BAND ENERGY LEVELS IN SUPERLATTICES WITH COMPLEX UNIT CELLS. Materials Research Society Symposia Proceedings, 1985, 56, 219.	0.1	3
11	Theoretical Methods for Calculating Electronic Properties of Semiconductor Superlattices. Materials Research Society Symposia Proceedings, 1985, 56, 279.	0.1	7
12	Zero Energy Gap Conditions and Band Inversion in Superlattices. Physica Status Solidi (B): Basic Research, 1985, 128, 575-581.	0.7	13
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20	ASPECTS OF THE THEORY OF SUPERLATTICES. , 1985, , 77-112.		3
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